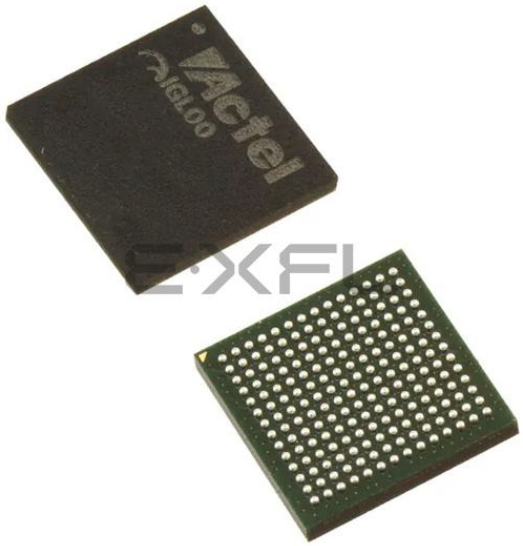

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	3072
Total RAM Bits	36864
Number of I/O	133
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	196-TFBGA, CSBGA
Supplier Device Package	196-CSP (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl125v5-csg196i

Table 2-10 • **Quiescent Supply Current (IDD) Characteristics, IGLOO Sleep Mode***

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
VCCI/VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI/VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI/VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI/VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI/VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	µA

Note: IDD = N_{BANKS} × ICCI. Values do not include I/O static contribution, which is shown in Table 2-13 on page 2-10 through Table 2-15 on page 2-11 and Table 2-16 on page 2-11 through Table 2-18 on page 2-12 (PDC6 and PDC7).

Table 2-11 • **Quiescent Supply Current (IDD) Characteristics, IGLOO Shutdown Mode**

	Core Voltage	AGL015	AGL030	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	µA

Table 2-12 • **Quiescent Supply Current (IDD), No IGLOO Flash*Freeze Mode[1]**

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
ICCA Current[2]										
Typical (25°C)	1.2 V	5	6	10	13	18	25	28	42	µA
	1.5 V	14	16	20	28	44	66	82	137	µA
ICCI or IJTAG Current[3]										
VCCI/VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI/VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI/VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI/VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI/VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	µA

Notes:

1. *IDD = N_{BANKS} × ICCI + ICCA. JTAG counts as one bank when powered.*
2. *Includes VCC, VPUMP, and VCCPLL currents.*
3. *Values do not include I/O static contribution (PDC6 and PDC7).*

Table 2-21 • **Different Components Contributing to Dynamic Power Consumption in IGLOO Devices For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Dynamic Power (µW/MHz)							
		AGL1000	**AGL600**	**AGL400**	**AGL250**	**AGL125**	**AGL060**	**AGL030**	**AGL015**
PAC1	Clock contribution of a Global Rib	4.978	3.982	3.892	2.854	2.845	1.751	0.000	0.000
PAC2	Clock contribution of a Global Spine	2.773	2.248	1.765	1.740	1.122	1.261	2.229	2.229
PAC3	Clock contribution of a VersaTile row	0.883	0.924	0.881	0.949	0.939	0.962	0.942	0.942
PAC4	Clock contribution of a VersaTile used as a sequential module	0.096	0.095	0.096	0.095	0.095	0.096	0.094	0.094
PAC5	First contribution of a VersaTile used as a sequential module	0.045							
PAC6	Second contribution of a VersaTile used as a sequential module	0.186							
PAC7	Contribution of a VersaTile used as a combinatorial module	0.158	0.149	0.158	0.157	0.160	0.170	0.160	0.155
PAC8	Average contribution of a routing net	0.756	0.729	0.753	0.817	0.678	0.692	0.738	0.721
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							
PAC11	Average contribution of a RAM block during a read operation	25.00							
PAC12	Average contribution of a RAM block during a write operation	30.00							
PAC13	Dynamic PLL contribution	2.10							

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

Table 2-22 • **Different Components Contributing to the Static Power Consumption in IGLOO Device For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage**

Parameter	Definition	Device Specific Static Power (mW)							
		AGL1000	**AGL600**	**AGL400**	**AGL250**	**AGL125**	**AGL060**	**AGL030**	**AGL015**
PDC1	Array static power in Active mode	See Table 2-12 on page 2-9.							
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-8.							
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7.							
PDC4	Static PLL contribution	0.90							
PDC5	Bank quiescent power (VCCI-Dependent)	See Table 2-12 on page 2-9.							
PDC6	I/O input pin static power (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PDC7	I/O output pin static power (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.

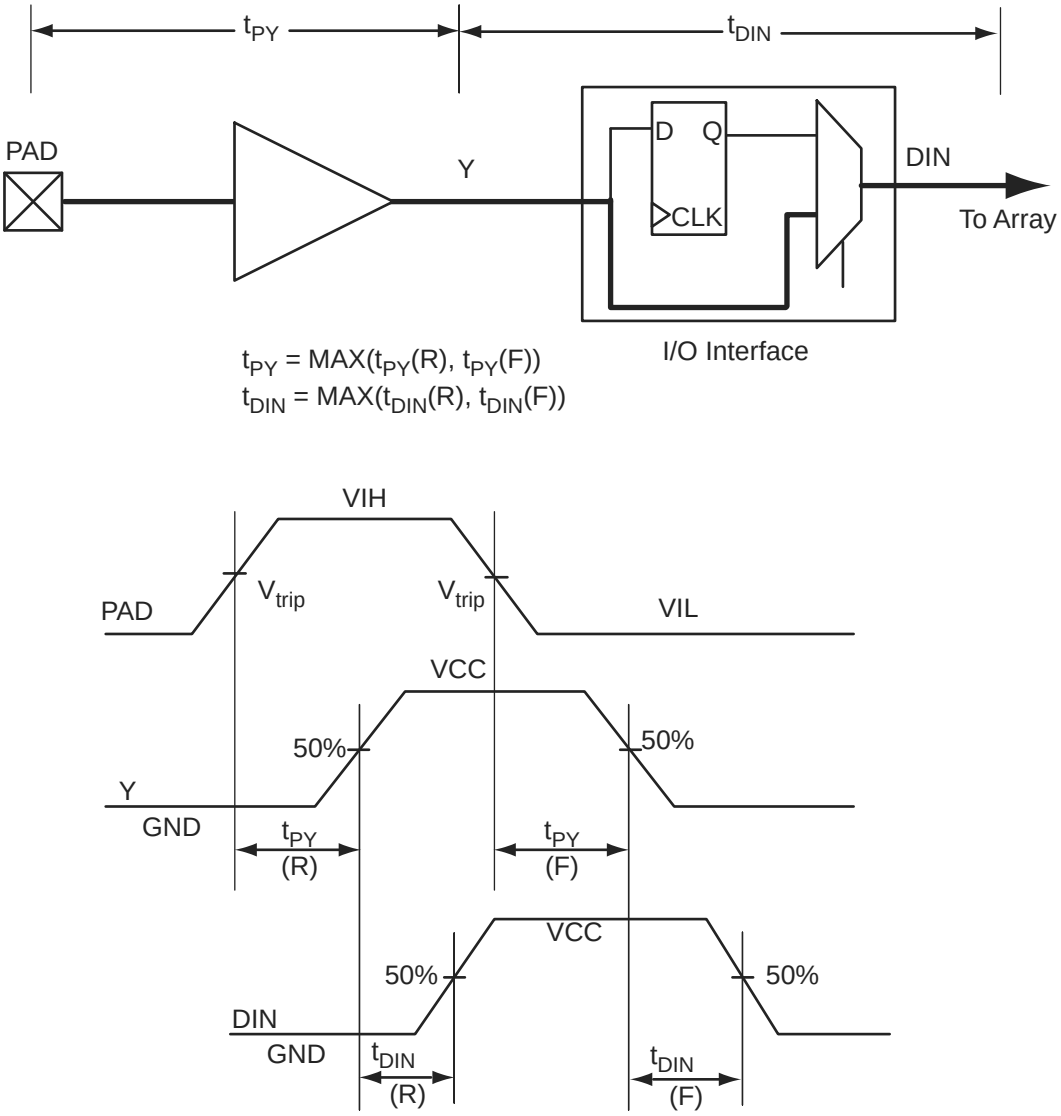

Figure 2-4 • **Input Buffer Timing Model and Delays (example)**

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-25 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings Applicable to Advanced I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[2]	Slew Rate	VIL		VIH		VOL	VOH	IOL[1]	IOH[1]
				Min.V	Max. V	Min. V	Max.V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range[3]	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	2.7	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	12 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	12	12
1.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	12	12
1.2 V LVCMOS[4]	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS Wide Range[4,5]	100 µA	2 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	1.575	0.1	VCCI – 0.1	0.1	0.1
3.3 V PCI	Per PCI specifications										
3.3 V PCI-X	Per PCI-X specifications										

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to V2 Devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-31 • **Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI (per standard) Applicable to Advanced I/O Banks**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1] (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12	High	5	–	0.97	2.09	0.18	0.85	0.66	2.14	1.68	2.67	3.05	5.73	5.27	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12	High	5	–	0.97	2.93	0.18	1.19	0.66	2.95	2.27	3.81	4.30	6.54	5.87	ns
2.5 V LVCMOS	12 mA	12	High	5	–	0.97	2.09	0.18	1.08	0.66	2.14	1.83	2.73	2.93	5.73	5.43	ns
1.8 V LVCMOS	12 mA	12	High	5	–	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns
1.5 V LVCMOS	12 mA	12	High	5	–	0.97	2.50	0.18	1.17	0.66	2.56	2.27	3.21	3.48	6.15	5.86	ns
3.3 V PCI	Per PCI spec	–	High	10	25 [2]	0.97	2.32	0.18	0.74	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 [2]	0.97	2.32	0.19	0.70	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns
LVDS	24 mA	–	High	–	–	0.97	1.74	0.19	1.35	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	0.97	1.68	0.19	1.16	–	–	–	–	–	–	–	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-97 • Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	2	2	9	11	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4	17	22	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

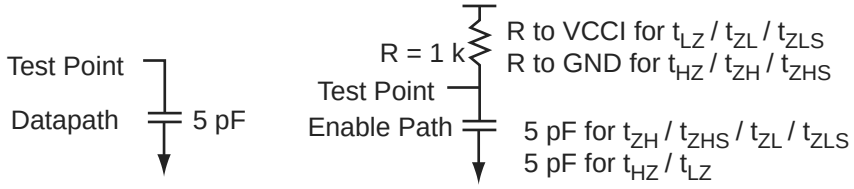

Figure 2-9 • AC Loading

Table 2-98 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.8	0.9	5

*Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-99 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	6.38	0.18	1.01	0.66	6.51	5.93	2.33	1.56	10.10	9.53	ns
4 mA	Std.	0.97	5.35	0.18	1.01	0.66	5.46	5.04	2.67	2.38	9.05	8.64	ns
6 mA	Std.	0.97	4.62	0.18	1.01	0.66	4.71	4.44	2.90	2.79	8.31	8.04	ns
8 mA	Std.	0.97	4.37	0.18	1.01	0.66	4.46	4.31	2.95	2.89	8.05	7.90	ns
12 mA	Std.	0.97	4.32	0.18	1.01	0.66	4.37	4.32	3.03	3.30	7.97	7.92	ns
16 mA	Std.	0.97	4.32	0.18	1.01	0.66	4.37	4.32	3.03	3.30	7.97	7.92	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

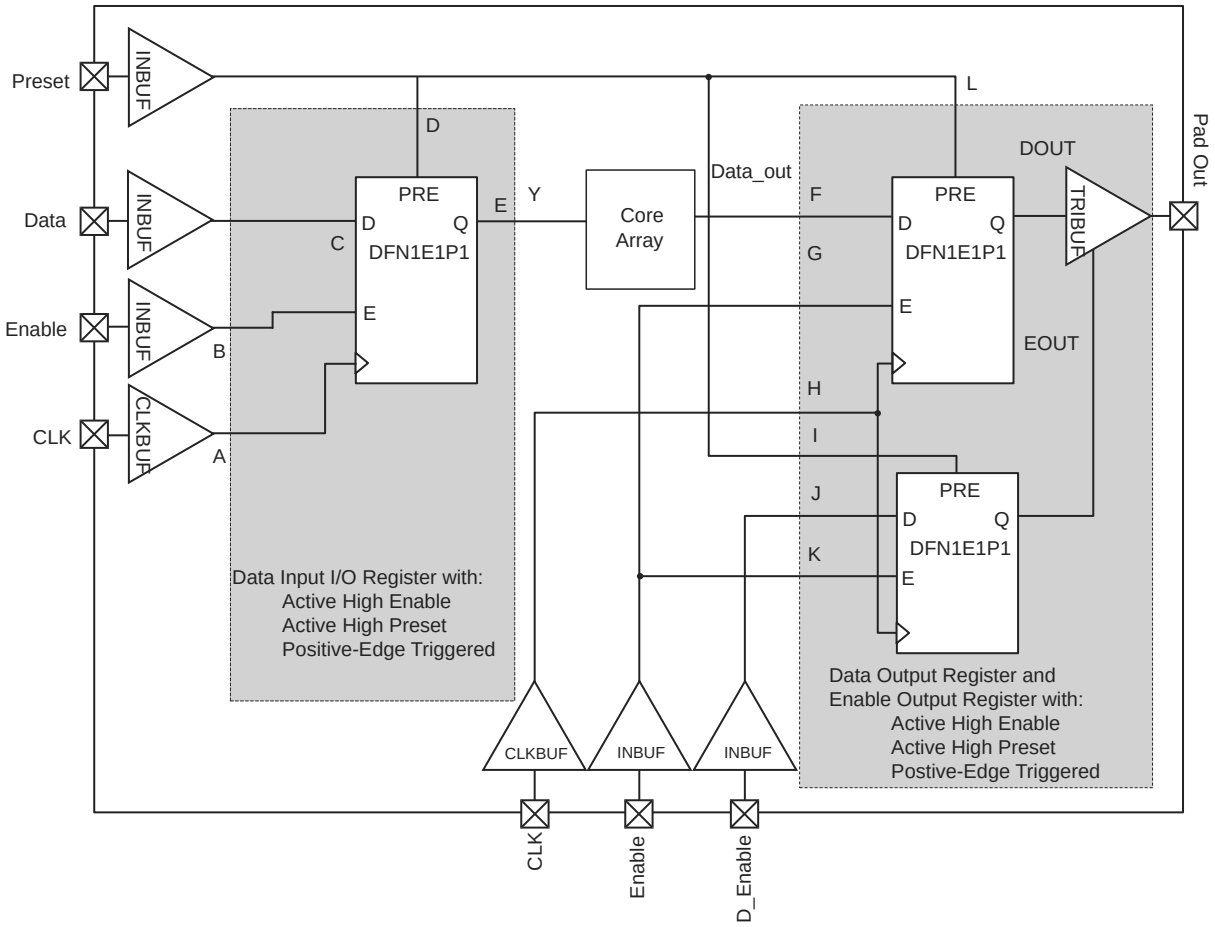

Figure 2-16 • **Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset**

Table 2-155 • **Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

*Note: *See Figure 2-16 on page 2-84 for more information.*

1.2 V DC Core Voltage

Table 2-165 • Input DDR Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR for Input DDR	0.76	ns
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF for Input DDR	0.94	ns
$t_{DDRISUD1}$	Data Setup for Input DDR (negedge)	0.93	ns
$t_{DDRISUD2}$	Data Setup for Input DDR (posedge)	0.84	ns
$t_{DDRIHD1}$	Data Hold for Input DDR (negedge)	0.00	ns
$t_{DDRIHD2}$	Data Hold for Input DDR (posedge)	0.00	ns
$t_{DDRICLR2Q1}$	Asynchronous Clear-to-Out Out_QR for Input DDR	1.23	ns
$t_{DDRICLR2Q2}$	Asynchronous Clear-to-Out Out_QF for Input DDR	1.42	ns
$t_{DDRIREMCLR}$	Asynchronous Clear Removal Time for Input DDR	0.00	ns
$t_{DDRIRECCLR}$	Asynchronous Clear Recovery Time for Input DDR	0.24	ns
$t_{DDRIWCLR}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
$t_{DDRICKMPWH}$	Clock Minimum Pulse Width High for Input DDR	0.31	ns
$t_{DDRICKMPWL}$	Clock Minimum Pulse Width Low for Input DDR	0.28	ns
$F_{DDRIMAX}$	Maximum Frequency for Input DDR	160.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Output DDR Module

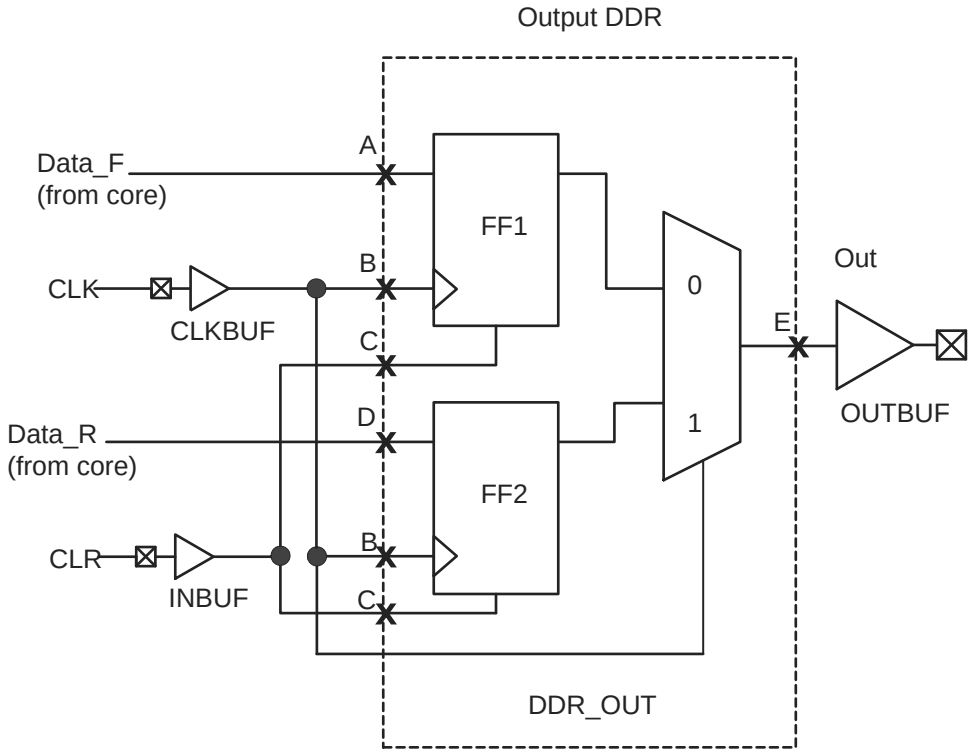

Figure 2-23 • **Output DDR Timing Model**

Table 2-166 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

1.2 V DC Core Voltage

***Table 2-193* • RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.53	ns
t_{AH}	Address hold time	0.29	ns
t_{ENS}	REN WEN setup time	1.50	ns
t_{ENH}	REN, WEN hold time	0.29	ns
t_{BKS}	BLK setup time	3.05	ns
t_{BKH}	BLK hold time	0.29	ns
t_{DS}	Input data (DIN) setup time	1.33	ns
t_{DH}	Input data (DIN) hold time	0.66	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	6.61	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	5.72	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	3.38	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address – Applicable to Closing Edge	0.30	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.89	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	1.01	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	3.86	ns
	RESET Low to data out Low on DOUT (pipelined)	3.86	ns
$t_{REMRSTB}$	RESET removal	1.12	ns
$t_{RECRSTB}$	RESET recovery	5.93	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

CS121	
Pin Number	**AGL060 Function**
K10	VPUMP
K11	GDB1/IO47RSB0
L1	VMV1
L2	GNDQ
L3	IO65RSB1
L4	IO63RSB1
L5	IO61RSB1
L6	IO58RSB1
L7	IO57RSB1
L8	IO55RSB1
L9	GNDQ
L10	GDA0/IO50RSB0
L11	VMV1

FG144	
Pin Number	**AGL600 Function**
K1	GEB0/IO145NDB3
K2	GEA1/IO144PDB3
K3	GEA0/IO144NDB3
K4	GEA2/IO143RSB2
K5	IO119RSB2
K6	IO111RSB2
K7	GND
K8	IO94RSB2
K9	GDC2/IO91RSB2
K10	GND
K11	GDA0/IO88NDB1
K12	GDB0/IO87NDB1
L1	GND
L2	VMV3
L3	FF/GEB2/IO142RSB2
L4	IO136RSB2
L5	VCCIB2
L6	IO115RSB2
L7	IO103RSB2
L8	IO97RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO141RSB2
M3	IO138RSB2
M4	IO123RSB2
M5	IO126RSB2
M6	IO134RSB2
M7	IO108RSB2
M8	IO99RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG256	
Pin Number	**AGL400 Function**
R5	IO123RSB2
R6	IO118RSB2
R7	IO112RSB2
R8	IO106RSB2
R9	IO100RSB2
R10	IO96RSB2
R11	IO89RSB2
R12	IO85RSB2
R13	GDB2/IO81RSB2
R14	TDI
R15	NC
R16	TDO
T1	GND
T2	IO126RSB2
T3	FF/GEB2/IO133RSB2
T4	IO124RSB2
T5	IO116RSB2
T6	IO113RSB2
T7	IO107RSB2
T8	IO105RSB2
T9	IO102RSB2
T10	IO97RSB2
T11	IO92RSB2
T12	GDC2/IO82RSB2
T13	IO86RSB2
T14	GDA2/IO80RSB2
T15	TMS
T16	GND

FG484	
Pin Number	**AGL400 Function**
N17	IO74RSB1
N18	IO72NPB1
N19	IO70NDB1
N20	NC
N21	NC
N22	NC
P1	NC
P2	NC
P3	NC
P4	IO142NDB3
P5	IO141NPB3
P6	IO125RSB2
P7	IO139RSB3
P8	VCCIB3
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB1
P16	GDB0/IO78VPB1
P17	IO76VDB1
P18	IO76UDB1
P19	IO75PDB1
P20	NC
P21	NC
P22	NC
R1	NC
R2	NC
R3	VCC
R4	IO140PDB3
R5	IO130RSB2
R6	IO138NPB3
R7	GEC0/IO137NPB3
R8	VMV3

FG484	
Pin Number	**AGL600 Function**
G5	IO171PDB3
G6	GAC2/IO172PDB3
G7	IO06RSB0
G8	GNDQ
G9	IO10RSB0
G10	IO19RSB0
G11	IO26RSB0
G12	IO30RSB0
G13	IO40RSB0
G14	IO45RSB0
G15	GNDQ
G16	IO50RSB0
G17	GBB2/IO61PPB1
G18	IO53RSB0
G19	IO63NDB1
G20	NC
G21	NC
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO166PDB3
H5	IO167NPB3
H6	IO172NDB3
H7	IO169NDB3
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO25RSB0
H12	IO31RSB0
H13	VCCIB0
H14	VCCIB0
H15	VMV1
H16	GBC2/IO62PDB1
H17	IO67PPB1
H18	IO64PPB1

FG484	
Pin Number	**AGL1000 Function**
V15	IO125RSB2
V16	GDB2/IO115RSB2
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	IO109NDB1
W1	NC
W2	IO191PDB3
W3	NC
W4	GND
W5	IO183RSB2
W6	FF/GEB2/IO186RSB2
W7	IO172RSB2
W8	IO170RSB2
W9	IO164RSB2
W10	IO158RSB2
W11	IO153RSB2
W12	IO142RSB2
W13	IO135RSB2
W14	IO130RSB2
W15	GDC2/IO116RSB2
W16	IO120RSB2
W17	GDA2/IO114RSB2
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB3
Y2	IO191NDB3
Y3	NC
Y4	IO182RSB2
Y5	GND
Y6	IO177RSB2

Revision	Changes	Page
Revision 21 (continued)	Pin description table for AGL125 CS121 was removed as it was incorrectly added to the datasheet in revision 19 (SAR 38217).	-
Revision 20 (March 2012)	Notes indicating that AGL015 is not recommended for new designs have been added. The "Devices Not Recommended For New Designs" section is new (SAR 35015).	I to IV
	Notes indicating that device/package support is TBD for AGL250-QN132 and AGL060-FG144 have been reinserted (SAR 33689).	I to IV
	Values for the power data for PAC1, PAC2, PAC3, PAC4, PAC7, and PAC8 were revised in Table 2-19 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices and Table 2-21 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices to match the SmartPower tool in Libero software version 9.0 SP1 and Power Calculator spreadsheet v7a released on 08/10/2010 (SAR 33768).	2-13, 2-15
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—PCLOCK" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the *IGLOO FPGA Fabric User Guide* (SAR 34730).	2-17
	Figure 2-4 • Input Buffer Timing Model and Delays (example) has been modified for the DIN waveform; the Rise and Fall time label has been changed to t_{DIN} (SAR 37104).	2-21
	Added missing characteristics for 3.3 V LVCMOS, 3.3 V LVCMOS Wide range, 1.2 V LVCMOS, and 1.2 V LVCMOS Wide range to the following tables: • Table 2-38, Table 2-39, Table 2-40, Table 2-42, Table 2-43, and Table 2-44 (SARs 33854 and 36891) • Table 2-63, Table 2-64, and Table 2-65 (SAR 33854) • Table 2-127, Table 2-128, Table 2-129, Table 2-137, Table 2-138, and Table 2-139 (SAR 36891).	2-35 to 2-40, 2-47 to 2-49, 2-74, 2-77, and 2-77
	AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match Table 2-50 · AC Waveforms, Measuring Points, and Capacitive Loads (SAR 34878).	2-42
	Added values for minimum pulse width and removed the FRMAX row from Table 2-173 through Table 2-188 in the "Global Tree Timing Characteristics" section. Use the software to determine the FRMAX for the device you are using (SAR 29271).	2-107 through 2-114
Revision 19 (September 2011)	CS121 was added to the product tables in the "IGLOO Low Power Flash FPGAs" section for AGL125 (SAR 22737). CS81 was added for AGL250 (SAR 22737).	I
	Notes indicating that device/package support is TBD for AGL250-QN132 and AGL060-FG144 have been removed (SAR 33689).	I to IV
	M1AGL400 was removed from the "I/Os Per Package1" table. This device was discontinued in April 2009 (SAR 32450).	II
	Dimensions for the QN48 package were added to Table 1 • IGLOO FPGAs Package Sizes Dimensions (SAR 30537).	II
	The Y security option and Licensed DPA Logo were added to the "IGLOO Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 32151).	III
	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 32865).	I, 1-2

Revision	Changes	Page
Revision 19 (continued)	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOO devices via an IEEE 1532 JTAG interface" (SAR 28756).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 21281).	1-8
	Values for VCCPLL at 1.2 V –1.5 V DC core supply voltage were revised in Table 2-2 • Recommended Operating Conditions 1 (SAR 22356). The value for VPUMP operation was changed from "0 to 3.45 V" to "0 to 3.6 V" (SAR 25220). The value for VCCPLL 1.5 V DC core supply voltage was changed from "1.4 to 1.6 V" to "1.425 to 1.575 V" (SAR 26551). The notes in the table were renumbered in order of their appearance in the table (SAR 21869).	2-2
	The temperature used in EQ 2 was revised from 110°C to 100°C for consistency with the limits given in Table 2-2 • Recommended Operating Conditions 1. The resulting maximum power allowed is thus 1.28 W. Formerly it was 1.71 W (SAR 26259).	2-6
	Values for CS196, CS281, and QN132 packages were added to Table 2-5 • Package Thermal Resistivities (SARs 26228, 32301).	2-6
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.425 V) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.14 V) were updated to remove the column for –20°C and shift the data over to correct columns (SAR 23041).	2-7
	The tables in the "Quiescent Supply Current" section were updated with revised notes on IDD (SAR 24112). Table 2-8 • Power Supply State per Mode is new.	2-7
	The formulas in the table notes for Table 2-41 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 21348).	2-37
	The row for 110°C was removed from Table 2-45 • Duration of Short Circuit Event before Failure. The example in the associated paragraph was changed from 110°C to 100°C. Table 2-46 • I/O Input Rise Time, Fall Time, and Related I/O Reliability1 was revised to change 110° to 100°C. (SAR 26259).	2-40
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section, "3.3 V LVCMOS Wide Range" section and "1.2 V LVCMOS Wide Range" section tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 25700).	2-28, 2-47, 2-77
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5 V–tolerant input buffer and push-pull output buffer."	2-56
	The values for $F_{DDRIMAX}$ and F_{DDOMAX} were updated in the tables in the "Input DDR Module" section and "Output DDR Module" section (SAR 23919).	2-94, 2-97
	The following notes were removed from Table 2-147 • Minimum and Maximum DC Input and Output Levels (SAR 29428): ±5% Differential input voltage = ±350 mV	2-81
	Table 2-189 • IGLOO CCC/PLL Specification and Table 2-190 • IGLOO CCC/PLL Specification were updated. A note was added to both tables indicating that when the CCC/PLL core is generated by Mircosemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-115